

# Reflective photosensor (photoreflector)

## RPR-220

The RPR-220 is a reflective photosensor. The emitter is a GaAs infrared light emitting diode and the detector is a high-sensitivity, silicon planar phototransistor. A custom lamp was developed to enable the achievement of a smaller package than with conventional reflectors.

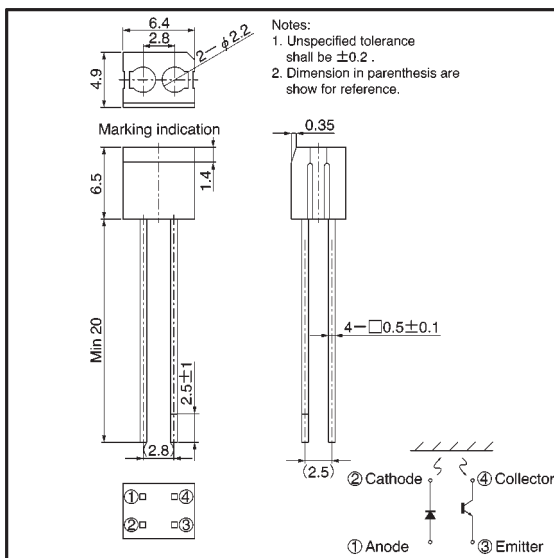
### ● Applications

Compact disk players, Copiers, Game machines,  
Office automation equipment

### ● Features

- 1) A plastic lens is used for high sensitivity.
- 2) A built-in visible light filter minimizes the influence of stray light.
- 3) Lightweight and compact.

### ● External dimensions (Units: mm)



### ● Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter		Symbol	Limits	Unit
Input(LED)	Forward current	$I_F$	50	mA
	Reverse voltage	$V_R$	5	V
	Power dissipation	$P_D$	80	mW
Output (photo-transistor)	Collector-emitter voltage	$V_{CEO}$	30	V
	Emitter-collector voltage	$V_{ECO}$	4.5	V
	Collector current	$I_C$	30	mA
	Collector power dissipation	$P_C$	80	mW
Operating temperature		$T_{opr}$	$-25 \sim +85$	$^\circ\text{C}$
Storage temperature		$T_{stg}$	$-30 \sim +85$	$^\circ\text{C}$

●Electrical and optical characteristics (Ta = 25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Input characteristics	Forward voltage	$V_F$	—	1.34	1.6	V	$I_F=50\text{mA}$
	Reverse current	$I_R$	—	—	10	$\mu\text{A}$	$V_R=5\text{V}$
Output characteristics	Dark current	$I_{CE0}$	—	—	0.5	$\mu\text{A}$	$V_{CE}=10\text{V}$
	Peak sensitivity wavelength	$\lambda_P$	—	800	—	nm	—
Transfer characteristics	Collector current	$I_C$	0.08	0.3	0.8	mA	$V_{CE}=2\text{V}, I_F=10\text{mA}$
	Collector-emitter saturation voltage	$V_{CE(sat)}$	—	0.1	0.3	V	$I_F=20\text{mA}, I_C=0.1\text{mA}$
	Response time	$tr \cdot tf$	—	10	—	$\mu\text{s}$	$V_{CC}=10\text{V}, I_F=20\text{mA}, R_L=100\Omega$

●Electrical and optical characteristic curves

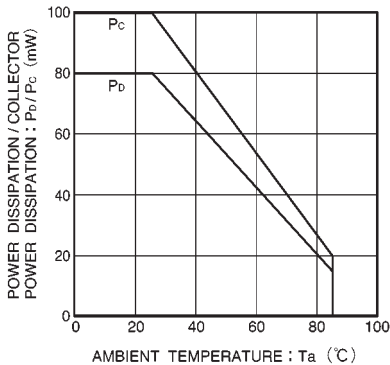


Fig.1 Power dissipation / collector power dissipation vs. ambient temperature

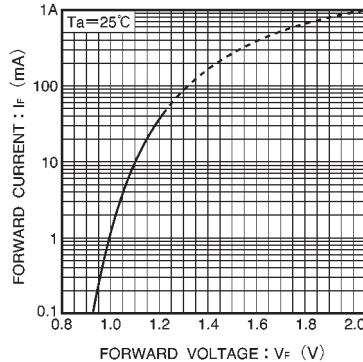


Fig.2 Forward current vs. forward voltage

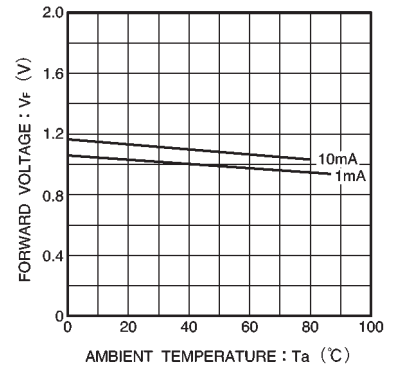


Fig.3 Forward voltage vs. ambient temperature

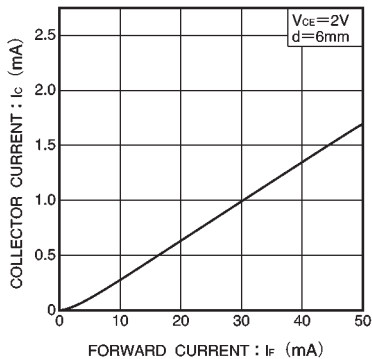


Fig.4 Collector current vs. forward current

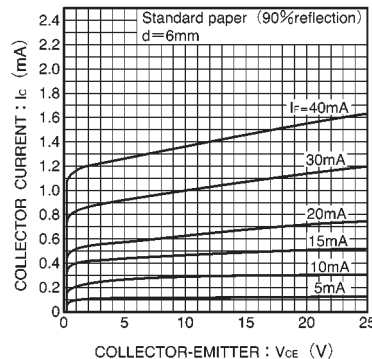


Fig.5 Output characteristics

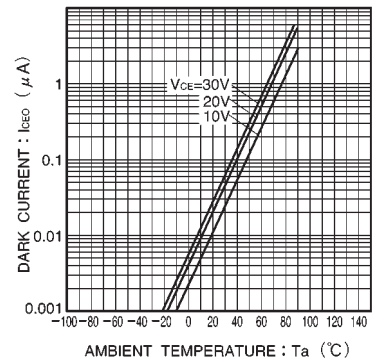


Fig.6 Dark current vs. ambient temperature

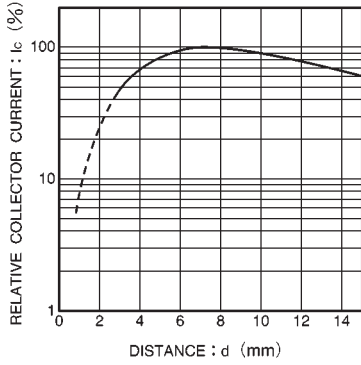


Fig.7 Relative output vs. distance

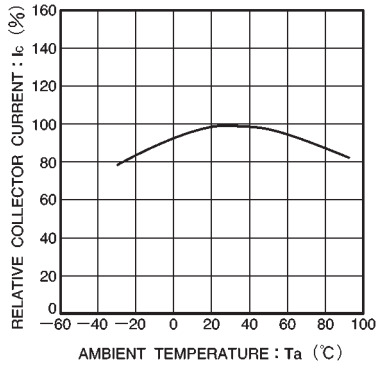


Fig.8 Relative output vs. ambient temperature

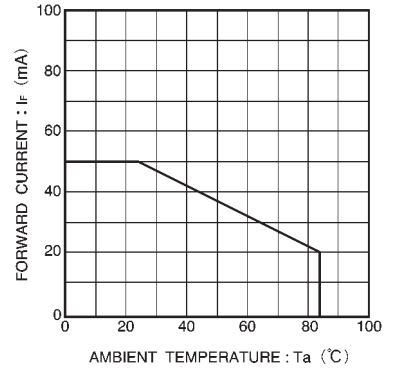


Fig.9 Forward current vs. ambient temperature

● Circuit for testing transfer characteristics

